NSN 5962-01-171-9685

Memory Microcircuit - Page 1 of 1

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Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Bipolar and programmable and hermetically sealed and high impedance and low level

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

6 input

Case Outline Source And Designator:

D-3 mil-m-38510

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Memory Device Type:

Rom

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0